Amendments to the Specification:

1. Please replace the title of the invention with the following amended title:

METHOD OF CORRECTING A MASK LAYOUT ~~CRITICAL DIMENSIONS OF ELEMENT PATTERNS ON A WAFER~~

2. Please replace paragraph [0002] with the following amended paragraph:

[0002] The present invention relates to a method of correcting ~~critical dimensions of element patterns on a wafer~~ a mask layout, and more particularly, to a method of correcting systematic errors produced during a pattern transfer process on ~~element patterns on a wafer~~ a mask layout.

3. Please replace paragraph [0010] with the following amended paragraph:

[0010] It is an objective of the claimed invention to provide a method of correcting ~~critical dimensions of element patterns on a wafer~~ a mask layout to effectively prevent micro-loading effect from inducing pattern transferring deviations.

4. Please replace paragraph [0011] with the following amended paragraph:

[0011] According to the claimed invention, a mask layout including a plurality of element patterns is provided. An ~~an~~ inspection program is executed to classify the element patterns of the [[a]] mask layout into a plurality of element pattern types according to ~~pattern deviation data of transferred element patterns onto a wafer~~ a pattern density of the element patterns. Following this, each of the element pattern types is corrected ~~and transferred to the wafer~~ so as to prevent a plasma micro-loading effect.

5. Please replace abstract of the present application with the following amended paragraph:

A method of correcting ~~critical dimensions of element patterns on a wafer~~ a mask layout is provided. The mask layout includes a plurality of element patterns. An inspection program is executed to classify the element patterns of the [[a]] mask layout into a plurality of element pattern types according to ~~pattern deviation data of transferred element patterns onto the wafer~~ a pattern density of the element patterns. Following this, each of the element pattern types is corrected ~~and transferred to the wafer~~ so as to prevent a plasma micro-loading effect.